

CORRECTION

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Correction: Exploring the feasibility and conduction mechanisms of P-type nitrogen-doped β -Ga₂O₃ with high hole mobility†

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Correction for 'Exploring the feasibility and conduction mechanisms of P-type nitrogen-doped β -Ga₂O₃ with high hole mobility' by Congcong Ma *et al.*, *J. Mater. Chem. C*, 2022, DOI: <https://doi.org/10.1039/d1tc05324h>.

The authors wish to point out that in the published article the footnote “[‡] These authors contributed equally to this work.” applies only to the authors Congcong Ma and Zhengyuan Wu.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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